

Photon detection systems

Fabrice Retiere (TRIUMF)

Work done within the TRIUMF astro-particle physics group

Collaboration with U.Sherbrooke (QC, Canada) for the Photon to Digital Converter

With support from TRIUMF Sci Tech dept and NSERC MRS and funding agencies:



Outline

- Light production in liquid Xenon
- Light detection with PMT
- Light detection with SiPMs
- Light detection with digital SiPMs

Light production

- Scintillation
 - Mean emission wavelength: 174.8 ± 0.14 nm
 - Width (sigma) of the distribution: 4.3 ± 0.1 nm
- Electroluminescence
- Cerenkov



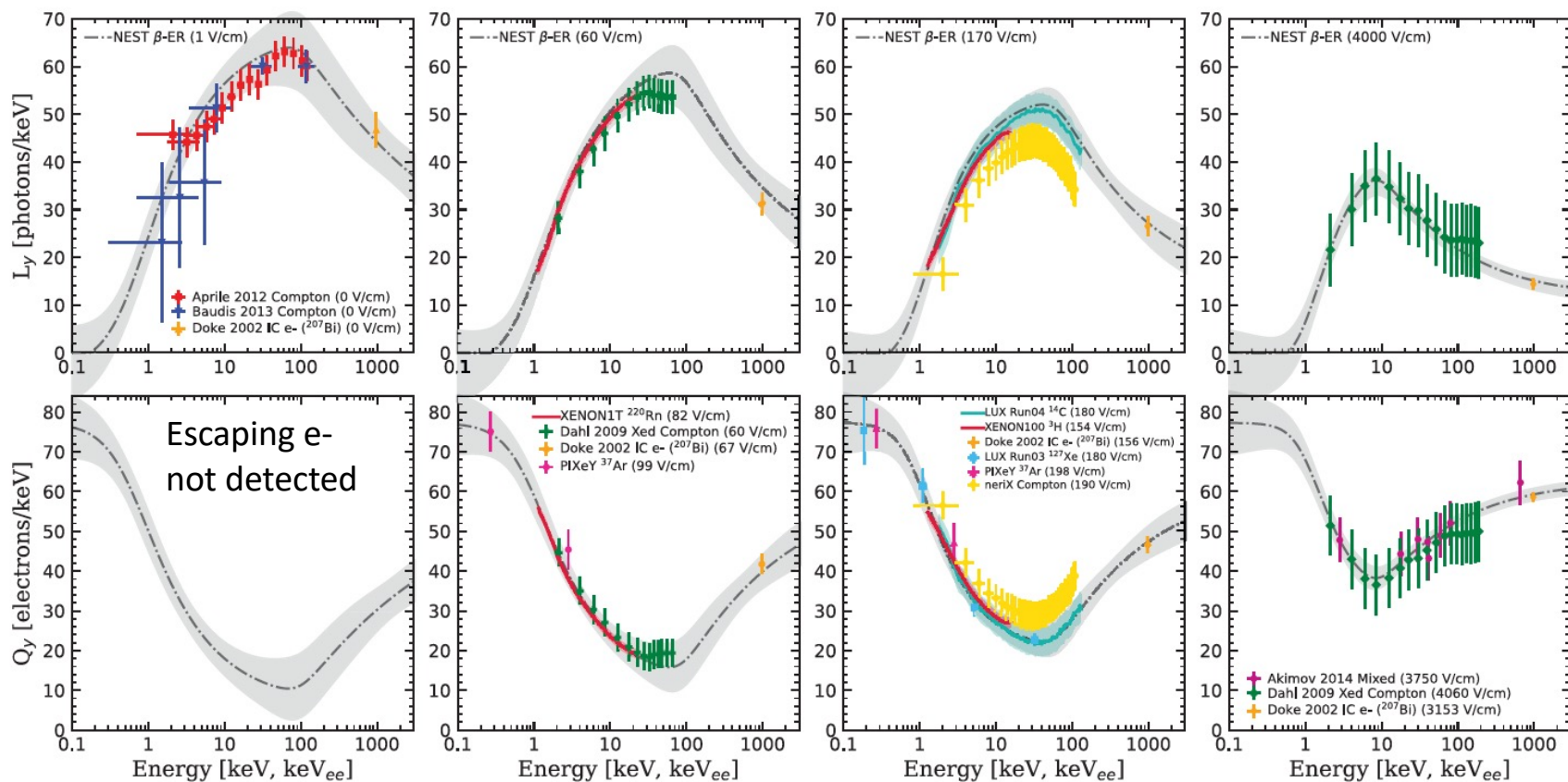
Nuclear Instruments and Methods in Physics
Research Section A: Accelerators, Spectrometers,
Detectors and Associated Equipment
Volume 795, 21 September 2015, Pages 293-297



High-accuracy measurement of the
emission spectrum of liquid xenon in the
vacuum ultraviolet region

Keiko Fujii^a, Yuya Endo^a, Yui Torigoe^a, Shogo Nakamura^a, Tomiyoshi Haruyama^b, Katsuyu
Kasami^b, Satoshi Mihara^{b,c}, Kiwamu Saito^{b,c}, Shinichi Sasaki^{b,c}, Hiroko Tawara^b

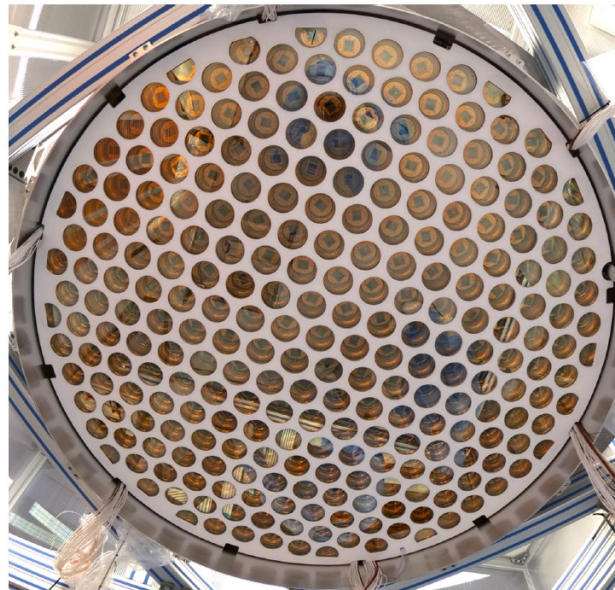
Scintillation light yield with e-/beta



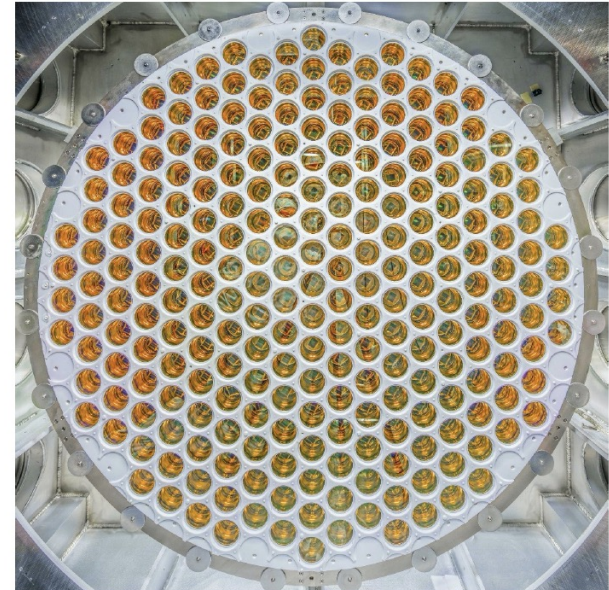
PMT
update
from
Laura
Baudis
(Zurich)

R11410 PMTs

- Baseline photosensor for XLZD: design book [arXiv:2410.17137](https://arxiv.org/abs/2410.17137)
- Efforts to reduce their overall activity



XENONnT



LZ

Nomenclature and further steps

PMT
update
from
Laura
Baudis
(Zurich)

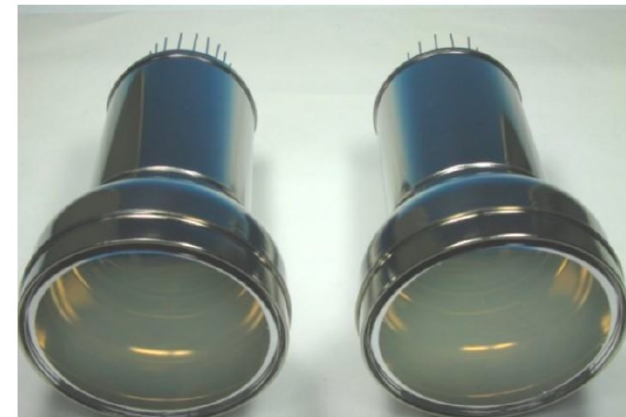
- PMT with metal stem with glass beads: **new name R17317**
- Further planned reduction in radioactivity
 - Photocathode with highly pure K used for XMASS (R13111)
 - Glass beads with low-radioactivity glass used for XMASS (R13111)

Also, we will test all 16 PMTs in GXe and LXe

R11410-21 and R17317



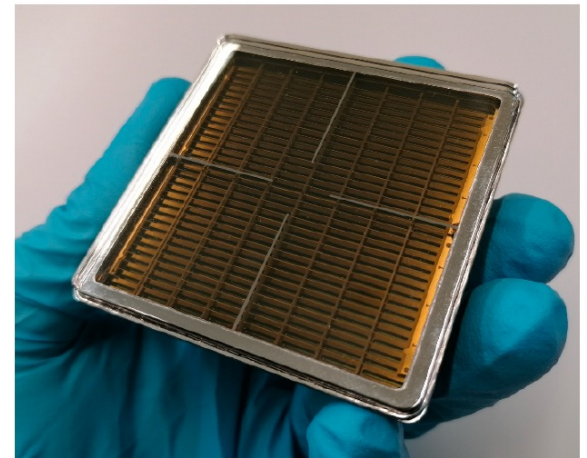
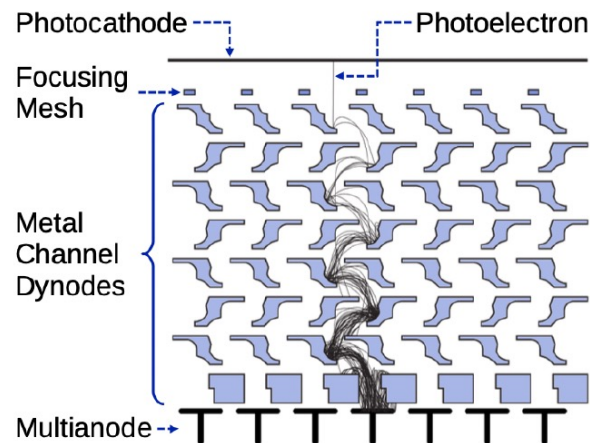
R11410-21 and R17317



The 2" square PMT

PMT
update
from
Laura
Baudis
(Zurich)

- Characterisation in LXe (MarmotX) and in a 2-phase TPC (Xams)
 - 2506.04844: UZH and Nikhef
 - screening with Gator
- Leakage issue around the pins (Hamamatsu aims to solve within 2025)



PMT
update
from
Laura
Baudis
(Zurich)

The 2" square PMT

● Comparison with the 3" unit

	R12699-406-M4	R11410-21
Dimensions (longitudinal / lateral)	14.8 mm / 56 mm [11]	114 mm / 77.5 mm [31]
Packing density	75.0 ‰	61.8 ‰
Dynode structure	Metal channel [11]	Box & linear-focused [31]
Number of dynode stages	10 [11]	12 [31]
Quantum efficiency at 175 nm	33 ‰ [11]	32.5 ‰ [31]
Operation voltage (nominal / max.)	1000 V / 1100 V [11]	1500 V / 1750 V [31]
Gain (T_{room})	$(3.3 \pm 0.7) \cdot 10^6$	$(8.4 \pm 2.3) \cdot 10^6$ [15]
SPE resolution (gain $\sim 2 \cdot 10^6$, T_{room})	$(37 \pm 3) \%$	$(30 \pm 3) \%$ [21]
Dark count rate ($> 1/4$ PE)	$(0.4 \pm 0.2) \text{ Hz/cm}^2$	$(1.4 \pm 0.7) \text{ Hz/cm}^2$ [21]
Time response (RT / transit time / TTS)	1.2 / 5.9 / 0.41 ns [11]	5.5 / 46 / 9 ns [31]
Separable afterpulse rate	$(1.1 \pm 0.2) \%$ /PE	$(8.6 \pm 2.2) \%$ /PE [21]

2506.04844

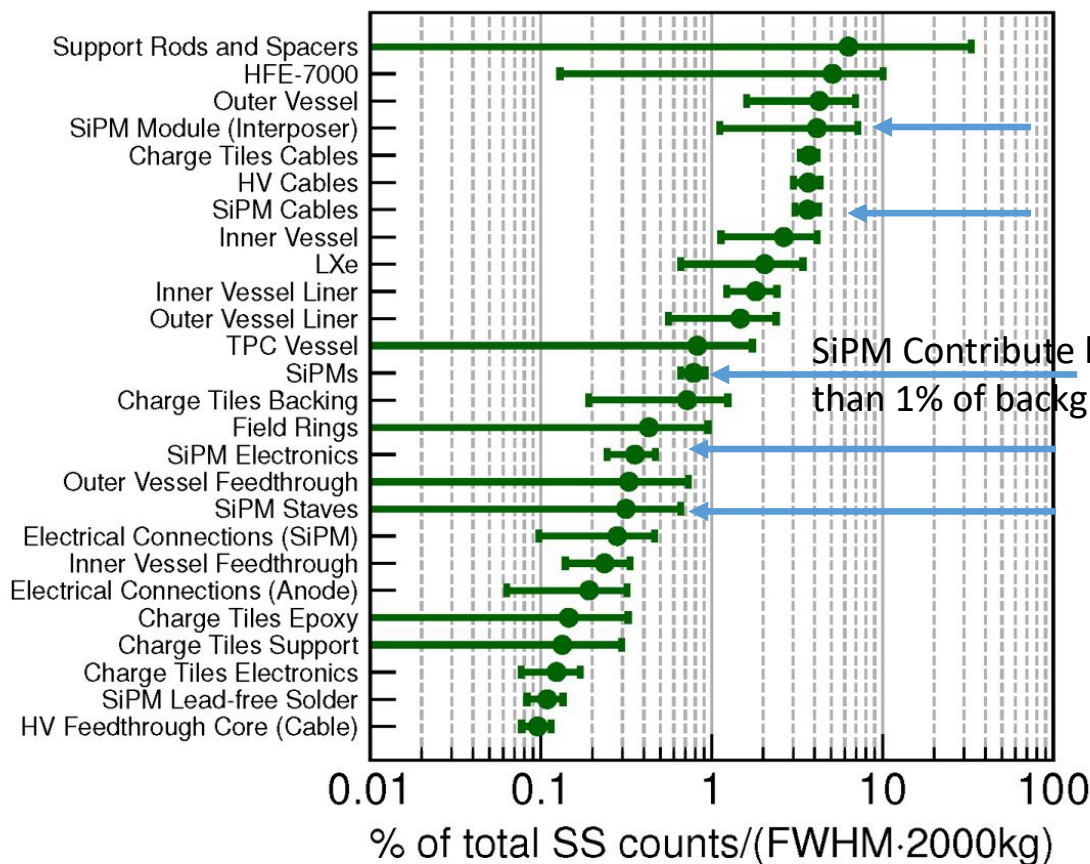
SiPM for lowest radioactivity content

PMT type	Normalized activity [mBq/cm ²]					60Co	Ref.
	²³⁸ U	²²⁶ Ra	²²⁸ Th	²³⁵ U	⁴⁰ K		
R11410-21	< 0.4	0.016(3)	0.012(3)	0.011(3)	0.37(6)	0.023(3)	this work
R11410-20	< 0.56	< 0.03	0.028(6)	< 0.025	0.37(6)	0.040(6)	this work
R11410-10	< 3.0	< 0.075	< 0.08	< 0.13	0.4(1)	0.11(2)	[20]
R11410-10 (PandaX)	–	< 0.02	< 0.02	0.04(4)	0.5(3)	0.11(1)	[12]
R11410-10 (LUX)	< 0.19	< 0.013	< 0.009	–	< 0.26	0.063(6)	[21]
R11410	1.6(6)	0.19(2)	0.09(2)	0.10(2)	1.6(3)	0.26(2)	[20]
R8778 (LUX)	< 1.4	0.59(4)	0.17(2)	–	4.1(1)	0.160(6)	[21]
R8520	< 0.33	0.029(2)	0.026(2)	0.009(2)	1.8(2)	0.13(1)	[20]

	²³⁸ U	²³² Th	⁴⁰ K
Prelim. nEXO requirements for 4m ²	< 0.1 nBq/cm ²	<1 nBq/cm ²	< 10 nBq/cm ²
Bare silicon VUV SiPM (FBK VUV-HD)	0.68 nBq/cm ²	0.12 nBq/cm ²	~3 nBq/cm ²
Packaged SiPM (SensL) ^a	<1.1 mBq/cm ²	<33 μBq/cm ²	<69 μBq/cm ²
Hamamatsu PMT R11410-21 ^b	<0.4 mBq/cm ²	0.016 mBq/cm ²	0.37 mBq/cm ²
Hamamatsu PMT HPK R12699-406-M4 ^c	0.02 mBq/cm ²	0.01 mBq/cm ²	1.5 mBq/cm ²

^a NEXT Ge counting. <http://arxiv.org/abs/1411.1433>
^b E. Aprile et al. Material radioassay and selection for the XENON1T dark matter experiment. Eur. Phys. J., C77(12):890, 2017, <https://arxiv.org/pdf/1705.01828.pdf>
^c Jiangia Liu’s PANDA-X talk yesterday

SiPM radiopurity is only part of the problem



- SiPMs are 2 to 3 orders of magnitude lower radioactivity than PMT
- But the system level is challenging. Need low radioactivity
 - Cables → kapton
 - PCB / interposer → SiO₂ or Si
 - Electronics → no package, all Si if possible

Using SiPM? Comparing all performances

Parameters at LXe temperature for cm ² scale channel size	PMT R11410- 21 ^a	FBK VUV-HD3 @ 3V ^b	HPK VUV4 MPPC @ 3V ^b
Single channel active area	128 cm ²	25 cm ² ^c	6 cm ² ^d
Efficiency at 175nm	34%	24.4 ± 1.4%	20.5 ± 1.1%
Single avalanche charge resolution	25%	5% ^c	5% ^d
Dark noise rate (Hz/cm ²)	1.3 ± 0.4	19 ± 1	35 ± 1
# correlated avalanche in 1 μs	0.02 ± 0.005	0.23 ± 0.06	0.06 ± 0.02
# Photons emitted per avalanche	N/A	1 ± 0.5	1 ± 0.5
Single photon timing resolution, σ	3.9 ± 0.6ns	~10 ns ^c	~100 ns ^d
Radiopurity per active area	~mBq/cm ²	Medium ^c	< 10 nBq/cm ² ^d
Power consumption in LXe	0.75 mW/cm ²	2 mW/cm ² ^c	2 mW/cm ² ^d

Compiled at XeSAT 2023

^a Massaged from P. Barrow et al., <https://arxiv.org/pdf/1609.01654.pdf>

^b G.Gallina et al., <https://arxiv.org/pdf/2209.07765.pdf>

^c DarkSide-20k readout scheme for 25 cm² channel size

^d nEXO readout scheme for 6 cm² channel size (can be applied to FBK)

But SiPMs distort the energy resolution

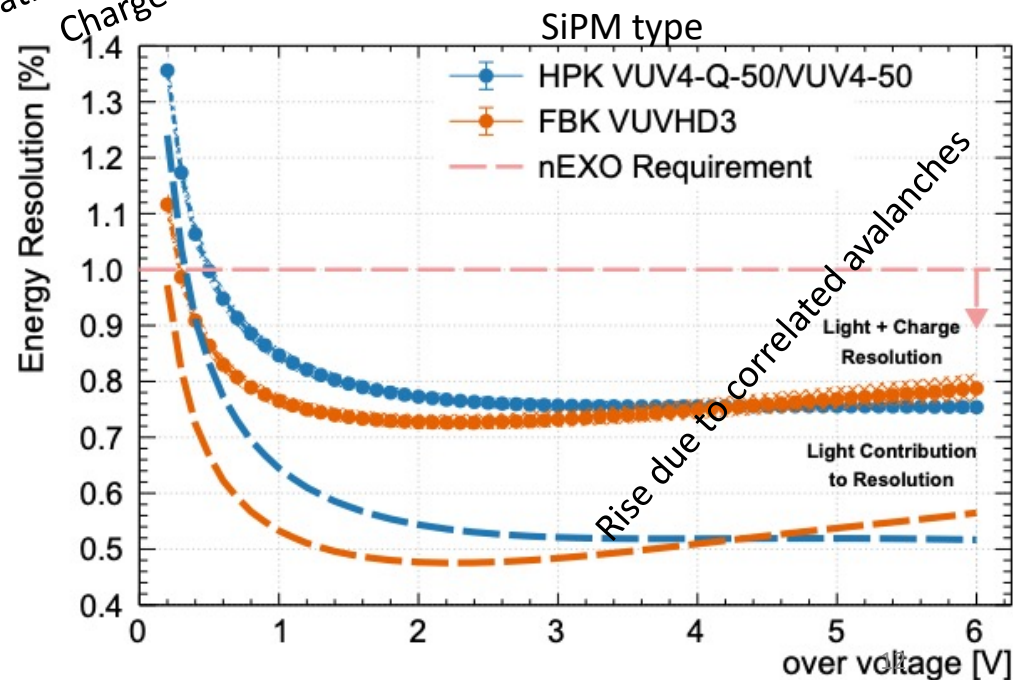
$$\frac{\sigma_n}{\langle n \rangle} = \frac{\sqrt{\left(\frac{(1-\epsilon_p)n_p}{\epsilon_p} + \frac{n_p}{\epsilon_p} \cdot \frac{\sigma_A^2}{(1+\langle \Lambda \rangle)^2} + n_p^2 \sigma_{lm}^2 \right) + \left(\frac{n_{qt}}{\tau} + \frac{\sigma_{q,noise}^2}{\epsilon_q^2} \right)}}{\langle n \rangle}$$

Efficiency contribution
Photo-detector correlated avalanche
(excess noise factor)

Light map calibration
Charge attenuation

Calculated for nEXO

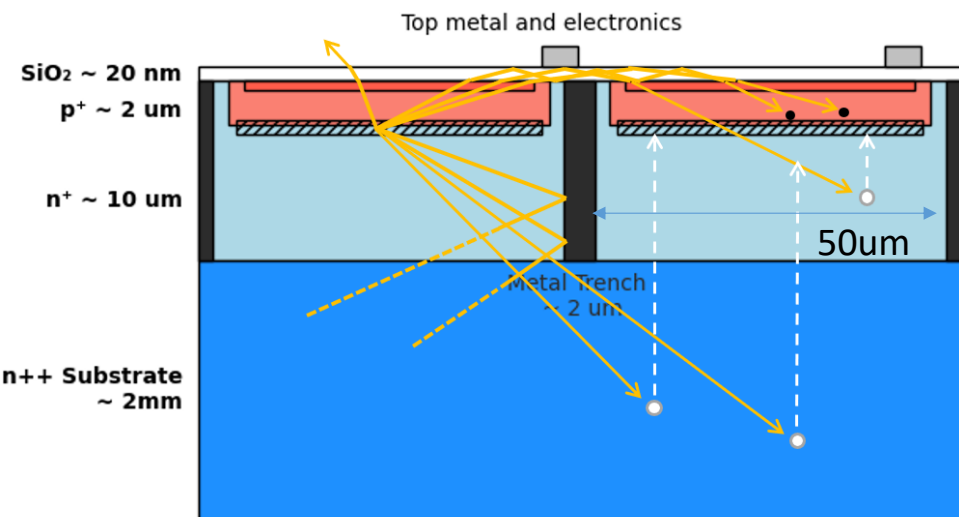
- Assumptions
 - Negligible intrinsic light+charge fluctuations
 - Photo-detector noise negligible
 - High gain
 - No external cross-talk considered



Parameter related to photo-detector bias

Light emission → internal cross-talk

HPK VUV4 SiPM Structure

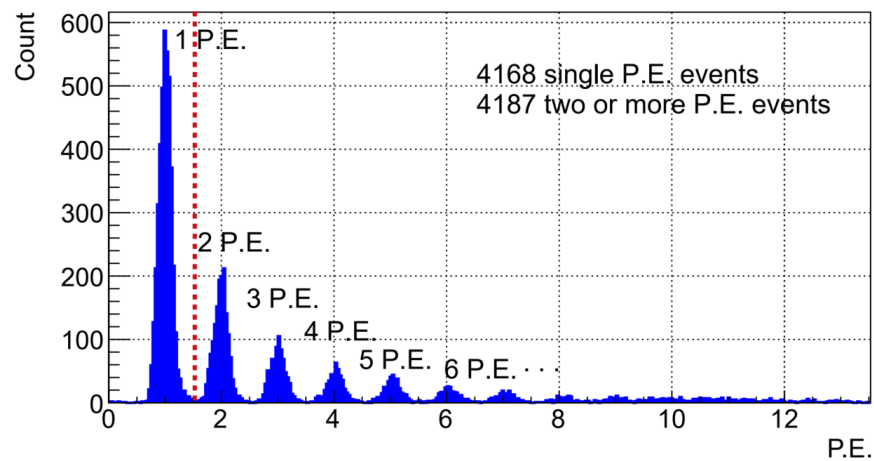


- Dark noise produce only one e-h pair at a time

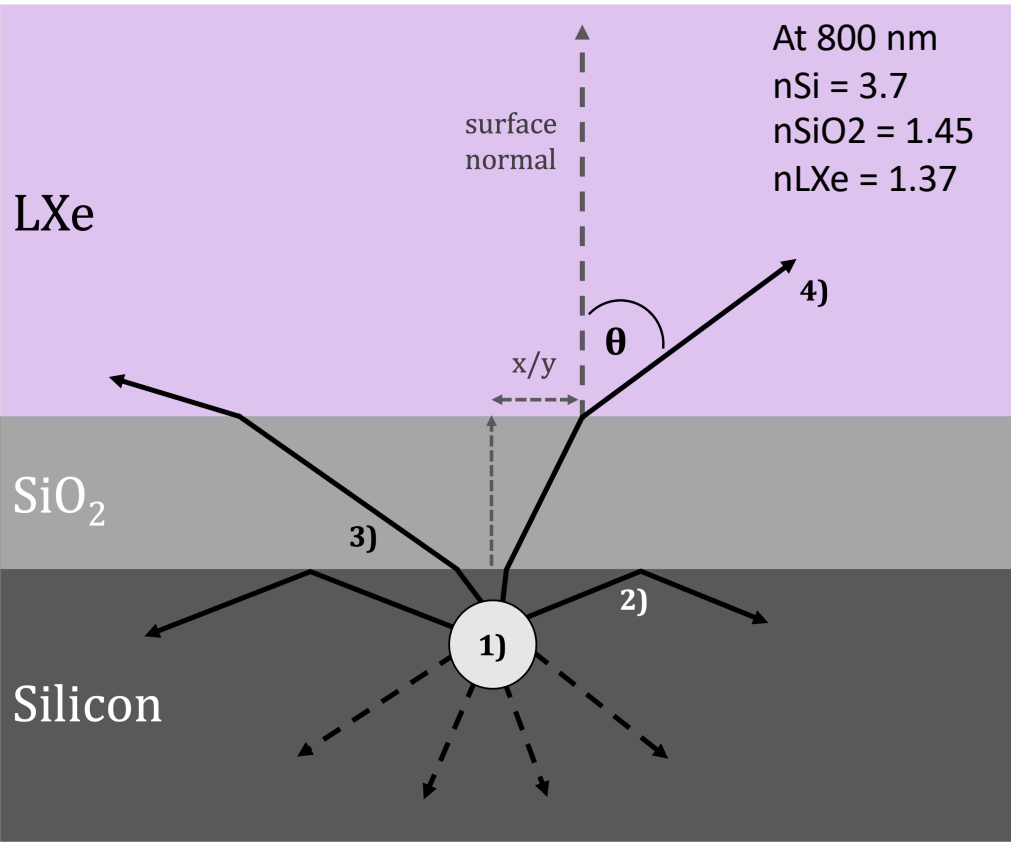
• electron

○ hole

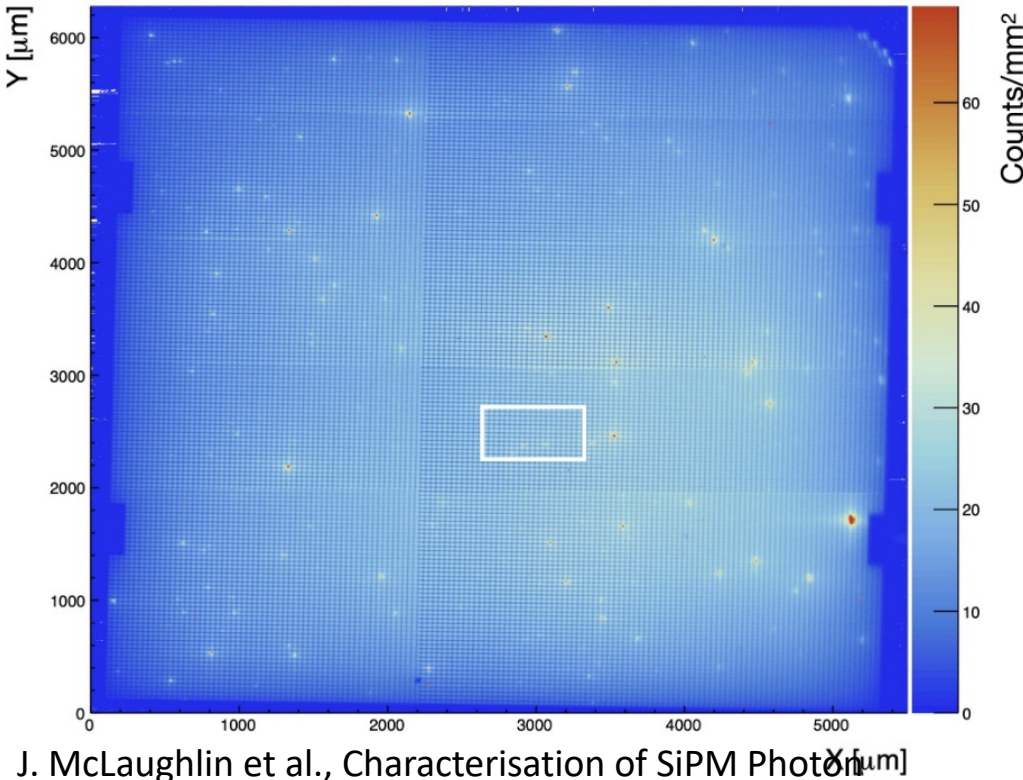
- Yet, it is common to measure > 1PE prompt = internal cross-talk



External cross-talk was a worry because its impact was unknown

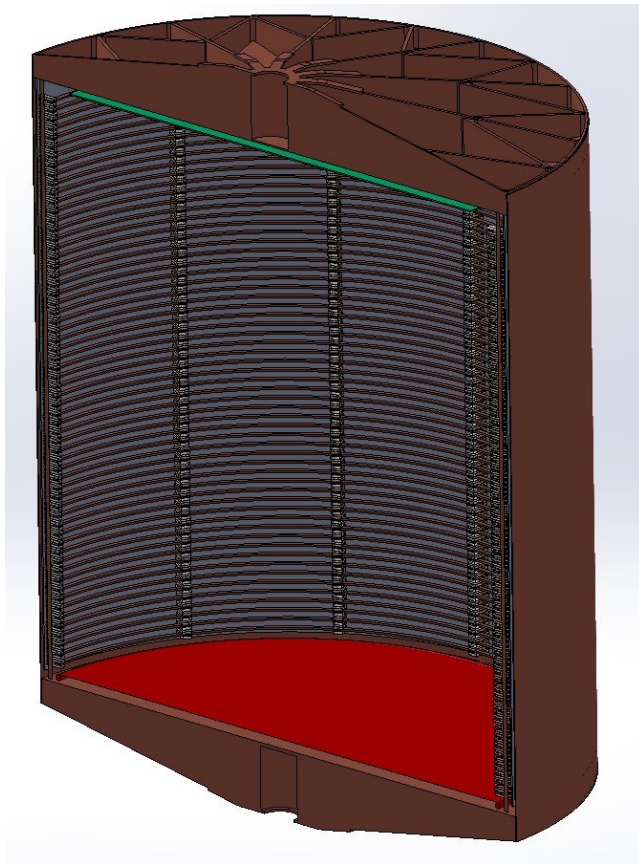


FBK emitting light in the dark

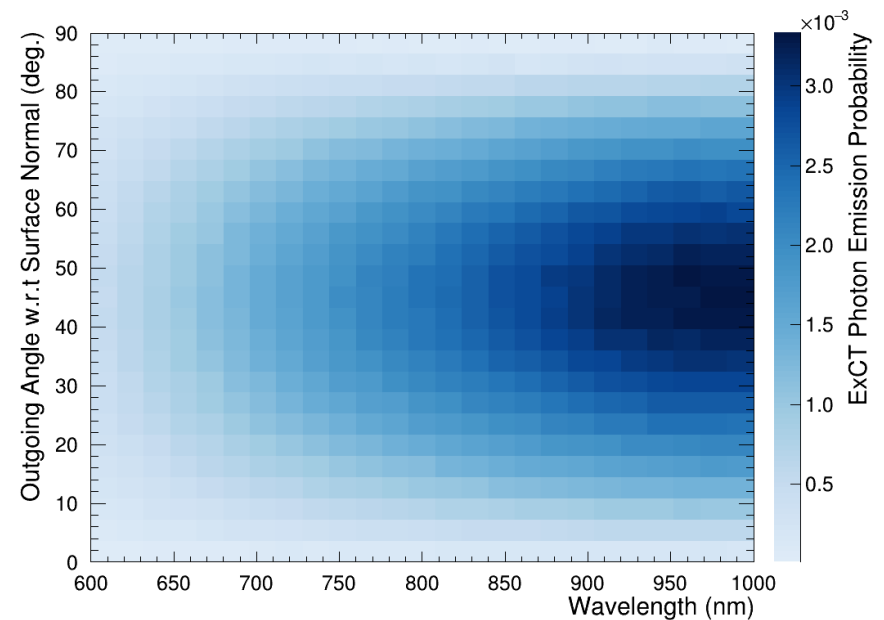


J. McLaughlin et al., Characterisation of SiPM Photon Emission in the Dark, *Sensors* **2021**, 21(17), 5947

External cross-talk is a worry when SiPM “face” each other

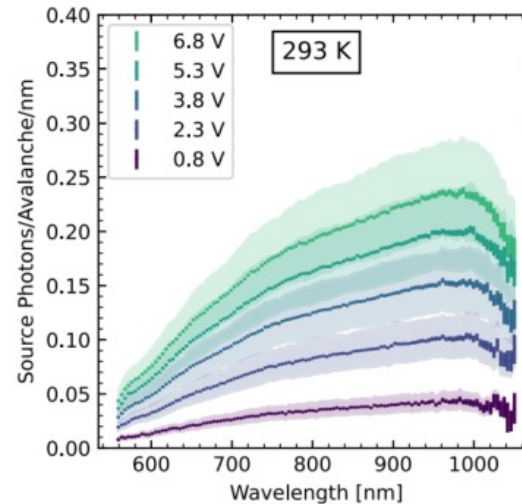


- Well, isotropic emission at source leads to large angle emission

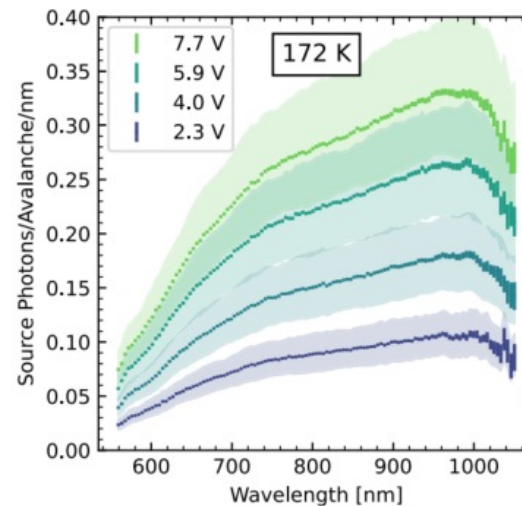


Hamamatsu VUV4

(a)

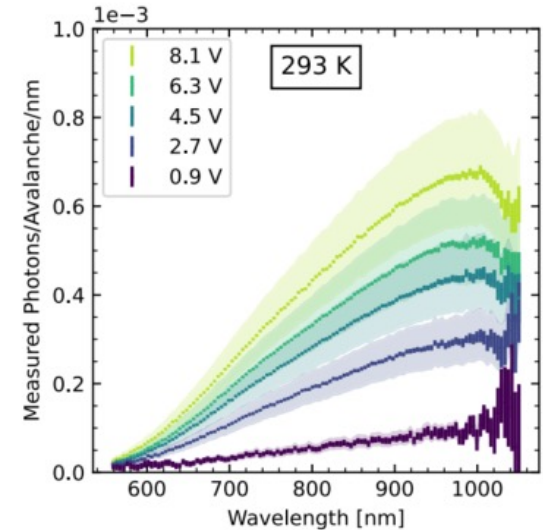


(c)

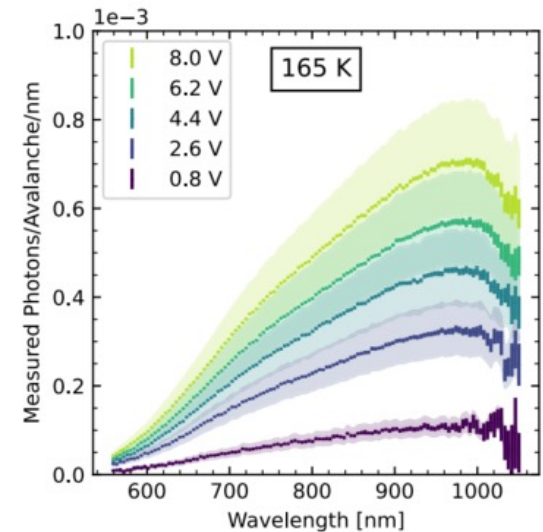


FBK VUV HD3

(b)



(d)



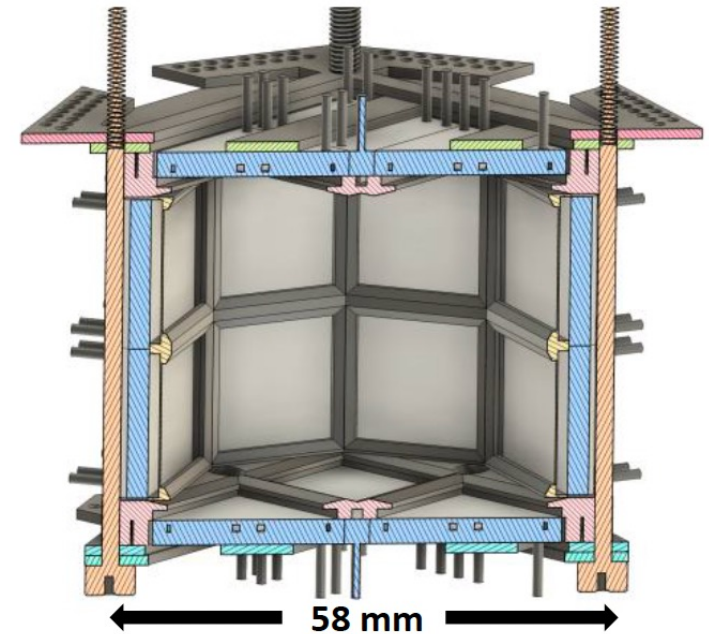
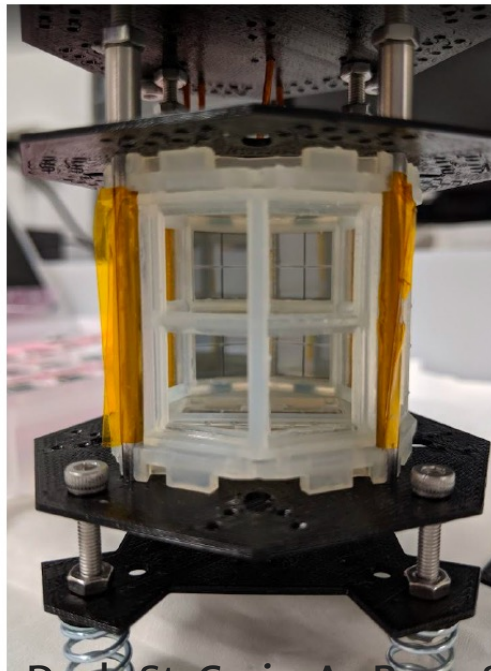
- Emission in Near Infra-red
- Photons per electron
 - $1.9 \pm 0.4 \cdot 10^{-5}$ for HPK VUV4
 - $2.6 \pm 0.5 \cdot 10^{-5}$ for FBK VUV-HD3
 - Same number?

K. Raymond *et al.*, "Stimulated Secondary Emission of Single-Photon Avalanche Diodes," in *IEEE Transactions on Electron Devices*, vol. 71, no. 11, pp. 6871-6879, Nov. 2024

Light emission → external cross-talk Probing the photons that escape with LoLX



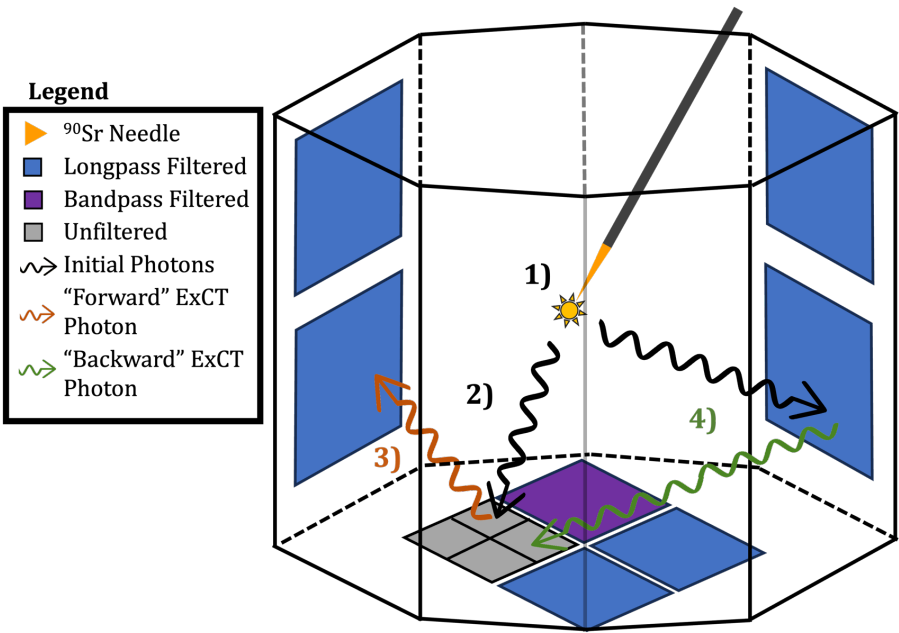
(From LoLX group pictures)



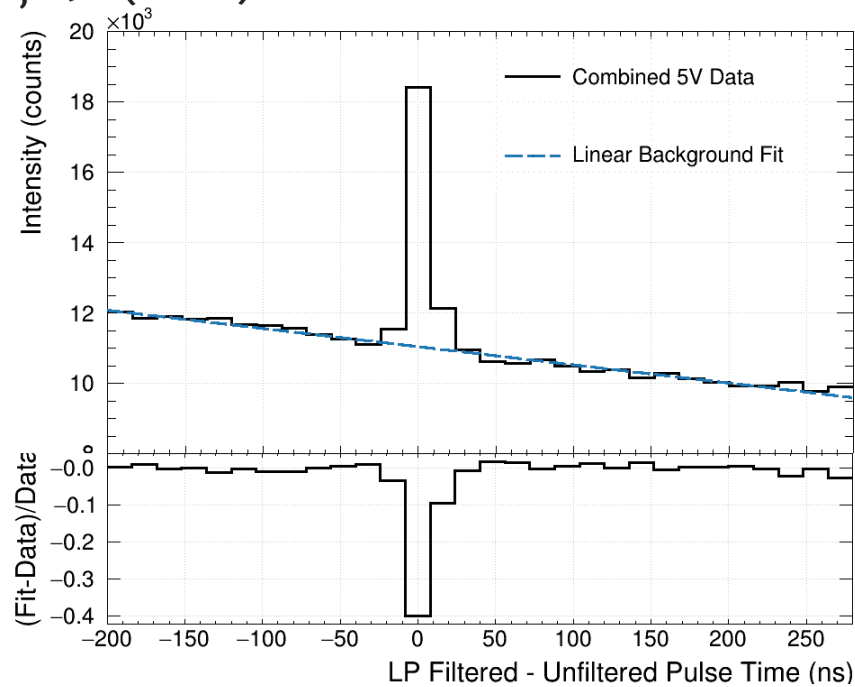
Gallacher, D., de St. Croix, A., Bron, S. *et al.* Characterization of external cross-talk from silicon photomultipliers in a liquid xenon detector. *Eur. Phys. J. C* 85, 692 (2025)

Light emission → external cross-talk

Use photons straggling after main scintillation event



Gallacher, D., de St. Croix, A., Bron, S. *et al.* Characterization of external cross-talk from silicon photomultipliers in a liquid xenon detector. *Eur. Phys. J. C* **85**, 692 (2025)



LoLX external cross-talk result

Overvoltage	Observable $P_{corr,B}$ (%)	ExCT probability (P_{Forw}) (%)	Emission within Si ($\gamma/\text{Av.}$)	Emission into LXe, N_{Xe} ($\gamma/\text{Av.}$)
4 V	3.9 ± 0.2 (stat.) $^{+0.5}_{-0.3}$ (sys.)	$2.1^{+1.2}_{-1.3}$	20^{+11}_{-9}	$0.5^{+0.3}_{-0.2}$
5 V	5.2 ± 0.2 (stat.) $^{+0.6}_{-0.4}$ (sys.)	2.6 ± 1.4	25^{+12}_{-9}	$0.6^{+0.3}_{-0.2}$

Probability that one avalanche by a SiPM

triggers one or more avalanche in any neighbors

- MIEL predicts 1.55 ∓ 0.62 photon emitted in liquid Xenon
- Acceptance about 50%
- Efficiency about 10%

Expected about 5%

Simulate

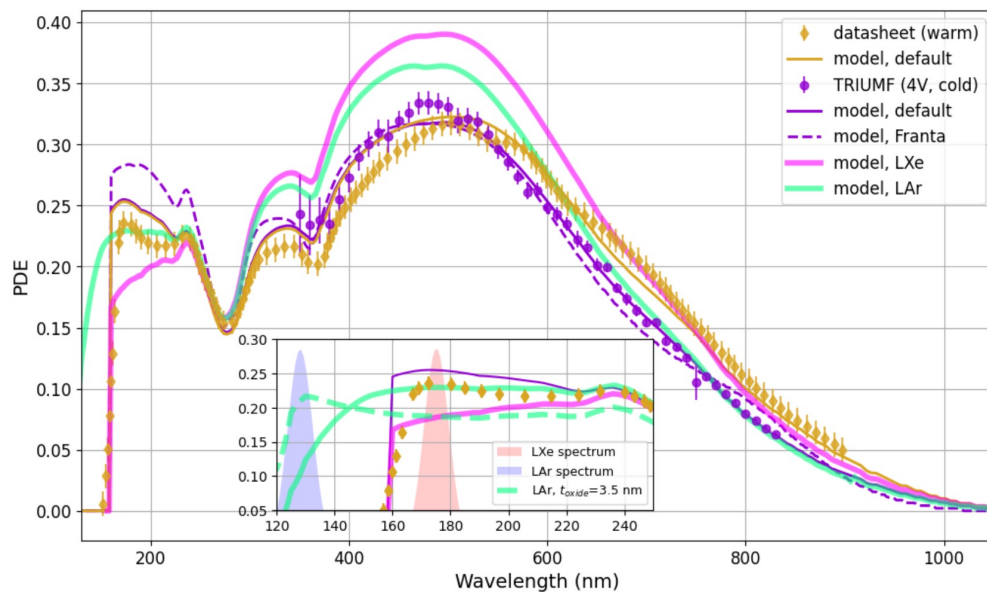
- Photon prod. using in Si isotropic assumption and spectrum from MIEL data
- Transport photons outside Si and within Lxe
- Use measured data for efficiency

Number in tension with MIEL predicted yield

Gallacher, D., de St. Croix, A., Bron, S. *et al.* Characterization of external cross-talk from silicon photomultipliers in a liquid xenon detector. *Eur. Phys. J. C* **85**, 692 (2025)

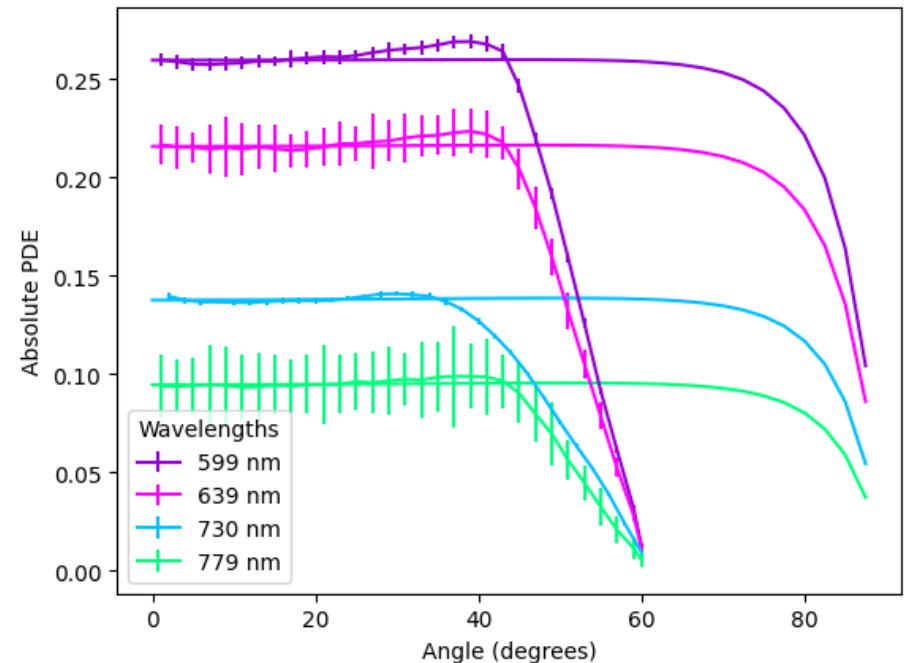
And to interpret cross-talk we had to look at near infra-red efficiency

- Need broadband
- Need angular dependence



A. de St. Croix et al., <https://arxiv.org/abs/2508.16005>

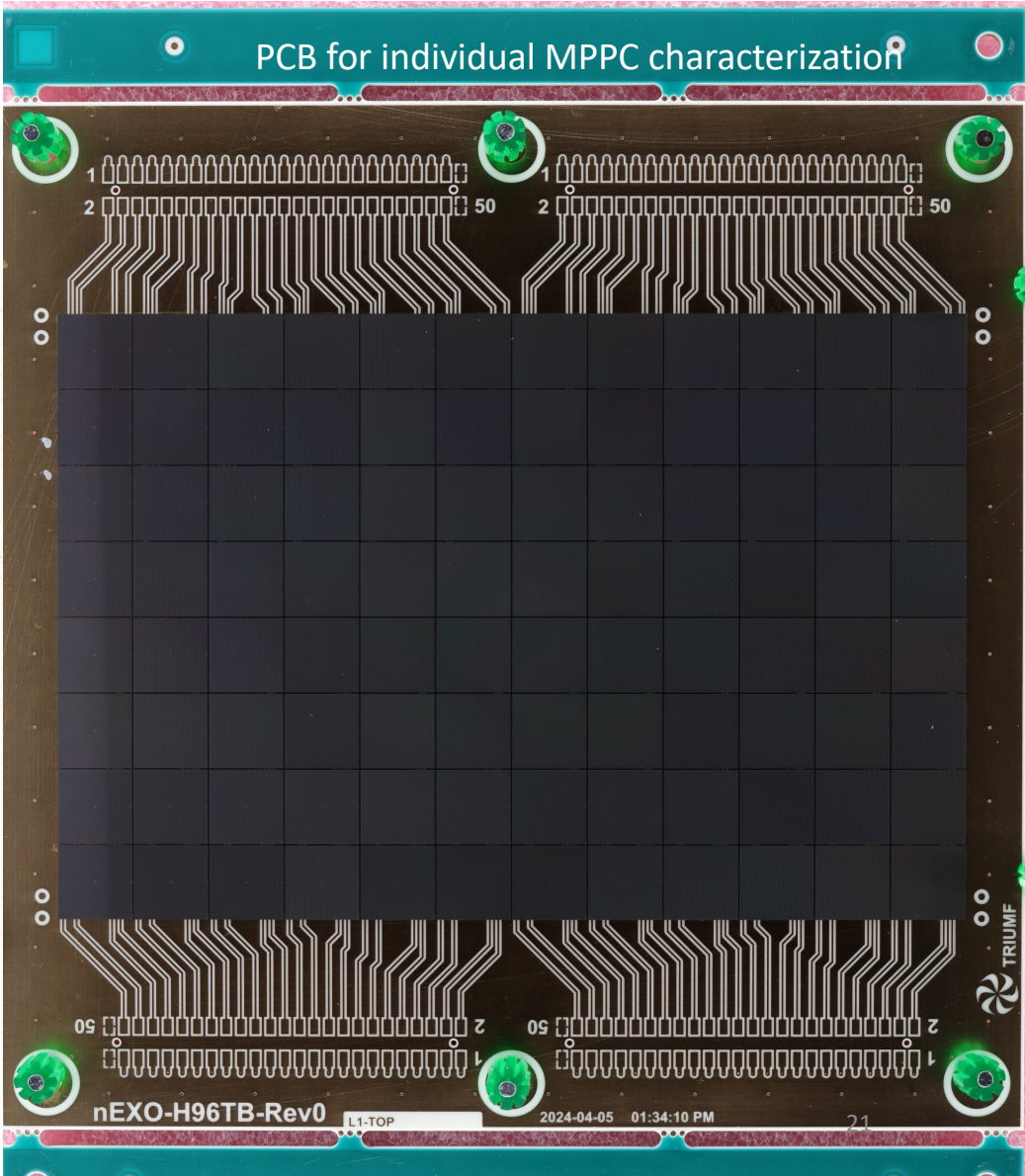
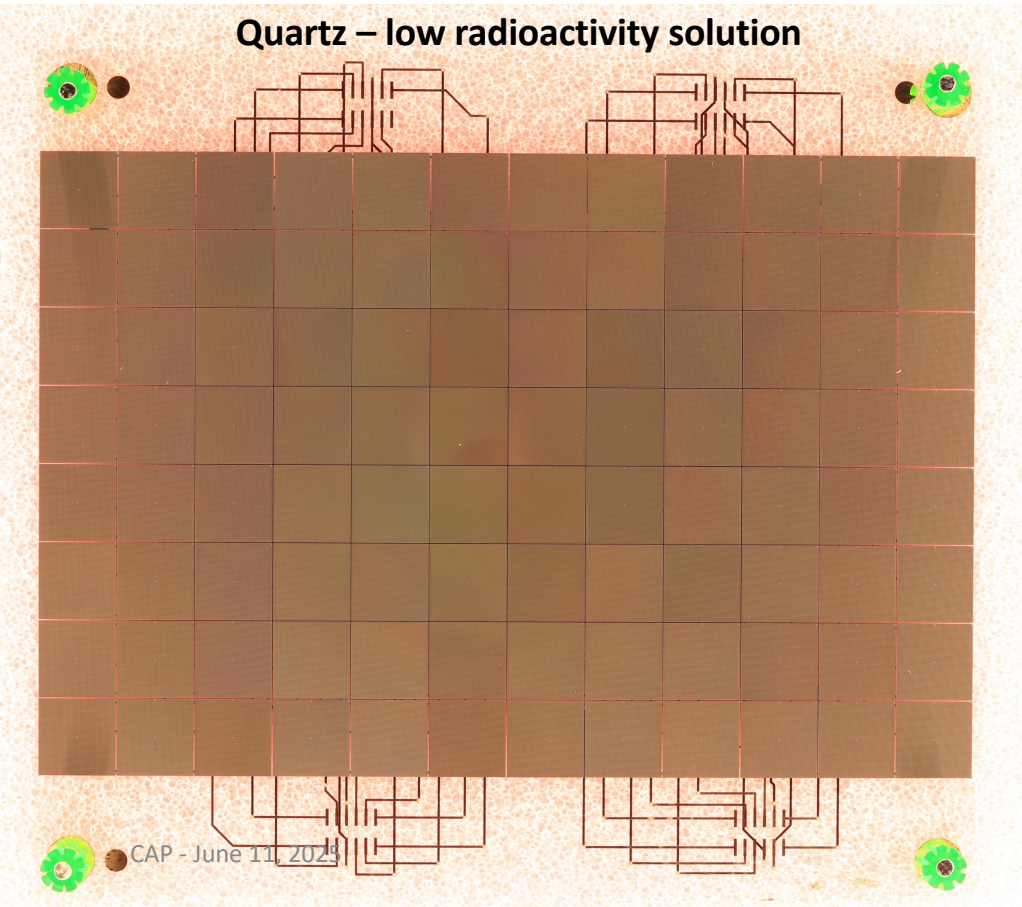
Trying to get this paper published





nEXO tiles – 12x8 1cm² Hamamatsu MPPC

Quartz – low radioactivity solution

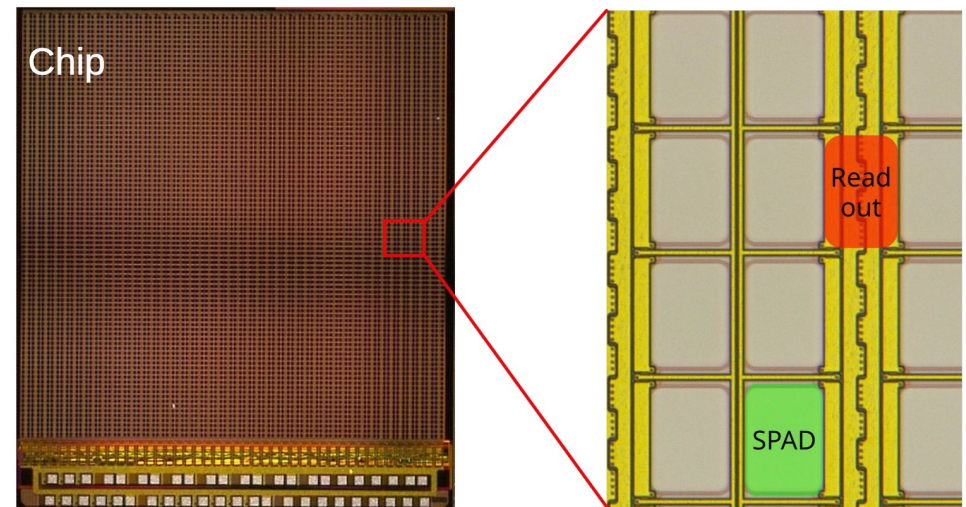


The next frontier: digital SiPM

- Pros
 - “no” power dissipation when idling
 - Tailor performances to needs. E.g. dynamic range, timing, imaging,...
 - Less complex at system level
- Cons
 - In 2D, some efficiency loss
 - More complex at chip level
 - Mass production not demonstrated

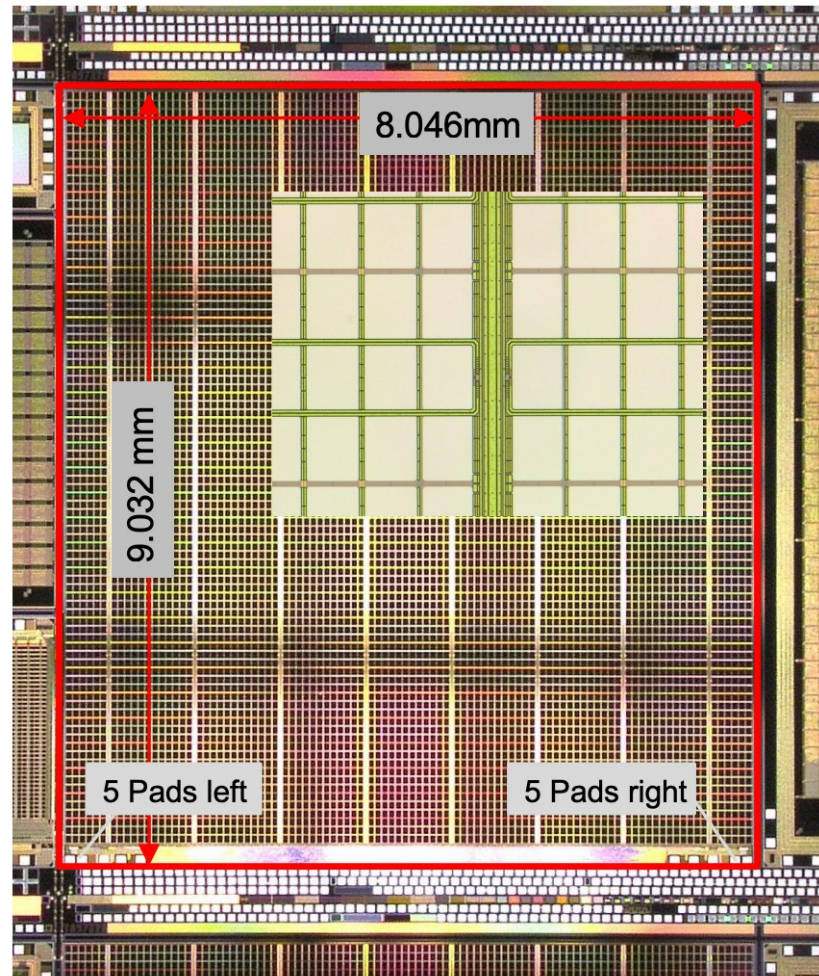
Digital SiPMs for DARWIN

Michael Keller, Peter Fischer, Robert Zimmermann, Michael Ritzert – University of Heidelberg
DARWIN Collaboration Meeting 2023 at University of Heidelberg

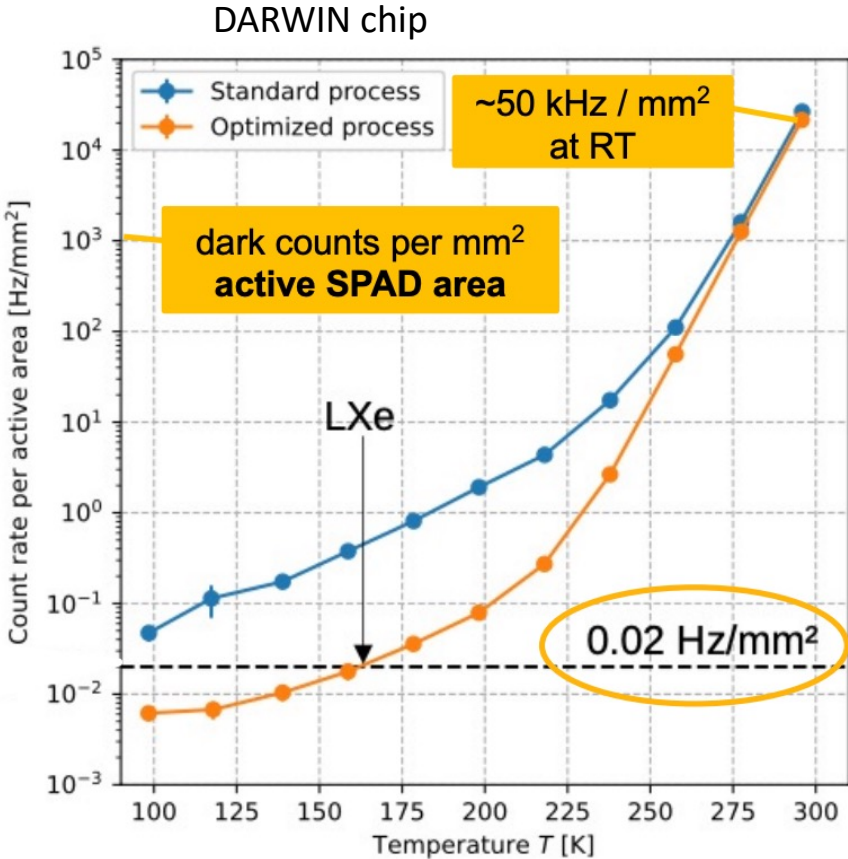


'DARWIN' Chip

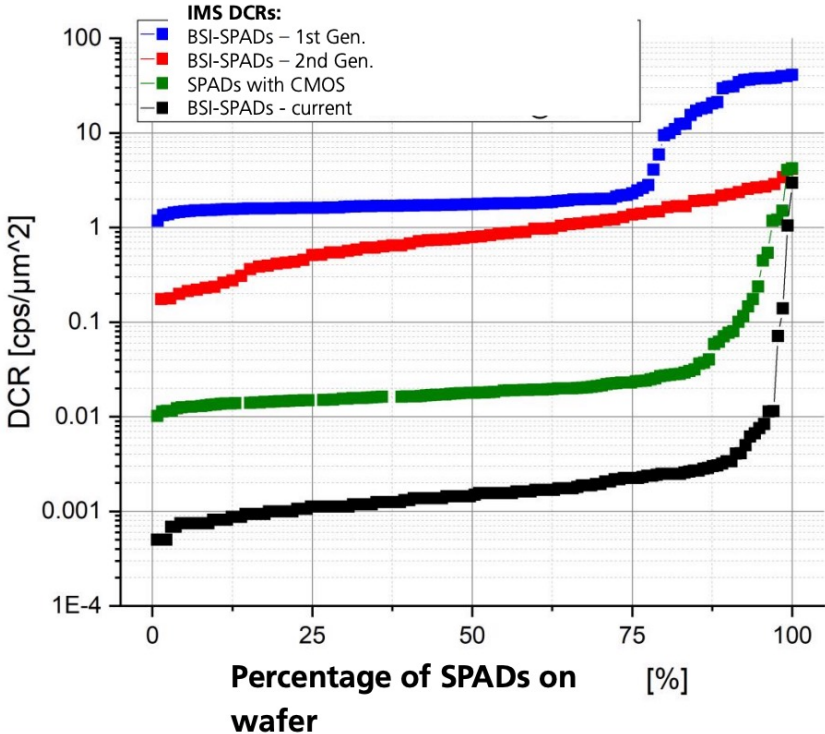
- Chip size: $\sim 8 \times 9 \text{ mm}^2$
- 32×30 pixels of $240 \times 290 \mu\text{m}^2$
 - One pixel contains 9 SPADs which can be masked individually (if noisy)
- SPAD active area fill factor $\sim 72\%$ (including periphery, before pixel masking)
- Only 7 chip signal:
 - 4 logic: Clk / Command / SerIn, SerOut
 - 3 supplies: GND, VDD, HV (pads duplicated)
- Manufactured at Fraunhofer IMS, Duisburg
 - 350nm CMOS Process, 4 metal layers
- P. F. et al, JINST 20, 2025
 - DOI 10.1088/1748-0221/20/06/C06008 (O.A.)



Dark count rate is coming down



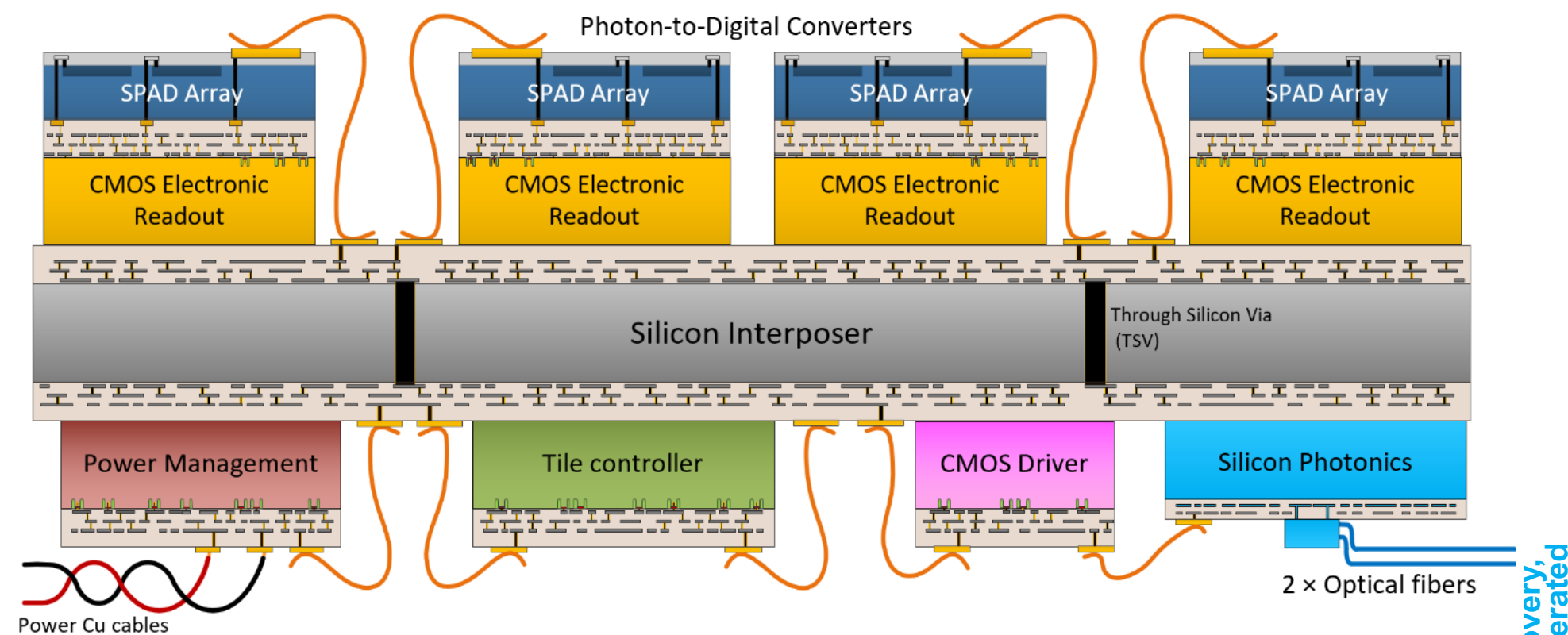
Latest Fraunhofer production at room temperature
Can reduce DCR by another order of magnitude by masking
Cost 20% PDE



However production issue

- Fraunhofer no longer offer the production line
- We are working on validating the X-FAB (Germany) SPAD line
 - Chip expected by mid-2026
- So, meanwhile in Canada, the photon to digital converter option is making major progress

Photon to Digital Converter – complete system



All silicon – ultra-low radioactivity solution

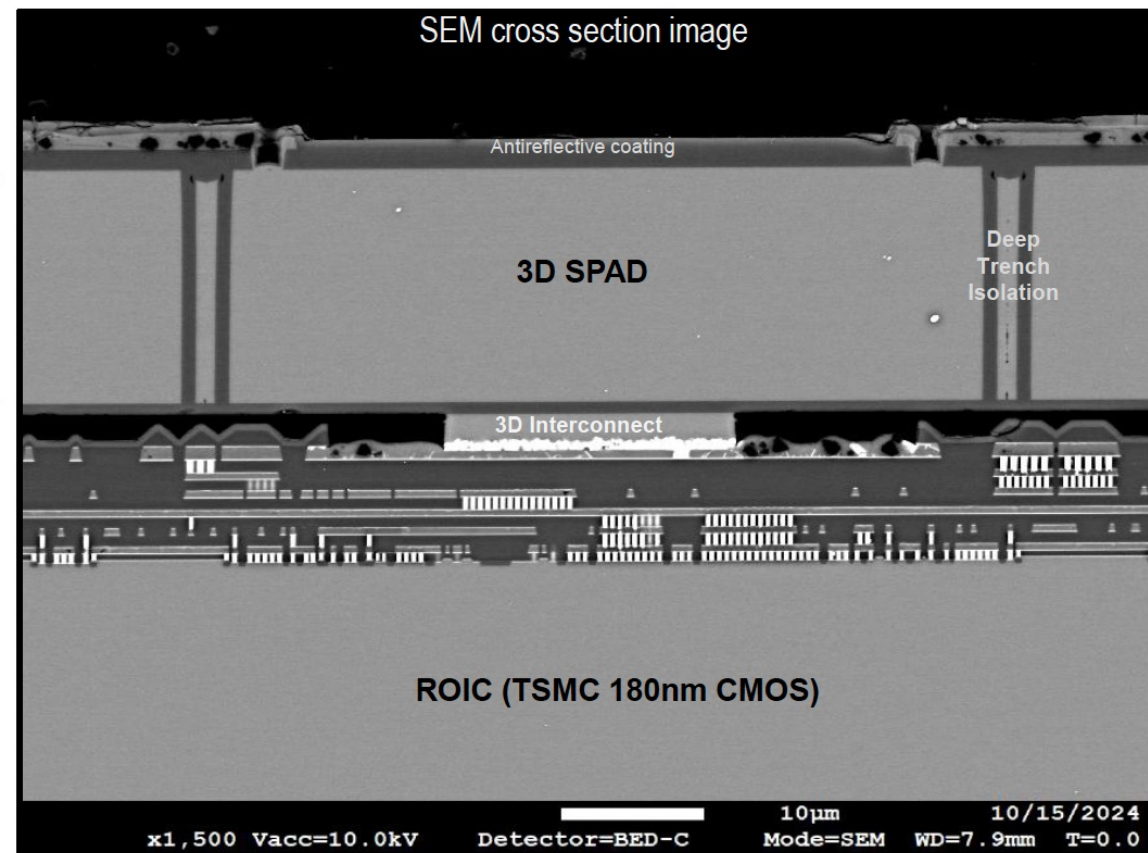
The Photon-to-Digital Converter – a thinned Frontside Illuminated SPAD Array

UDS

2nd run of improved devices delivered on April 2025

- p⁺n SPAD [1]
- **64 × 64 SPAD Array**
- **78 μm pitch** (FF = 26.2%)
- 5.85 × 5.25 mm² die
- Peak photon detection probability (PDP) :
 - 60% @ 420 nm → PDE = 15.8%
 - >10% @ 400-800 nm
- **Low power CMOS optimisation** dedicated to high energy physics applications

20 μm



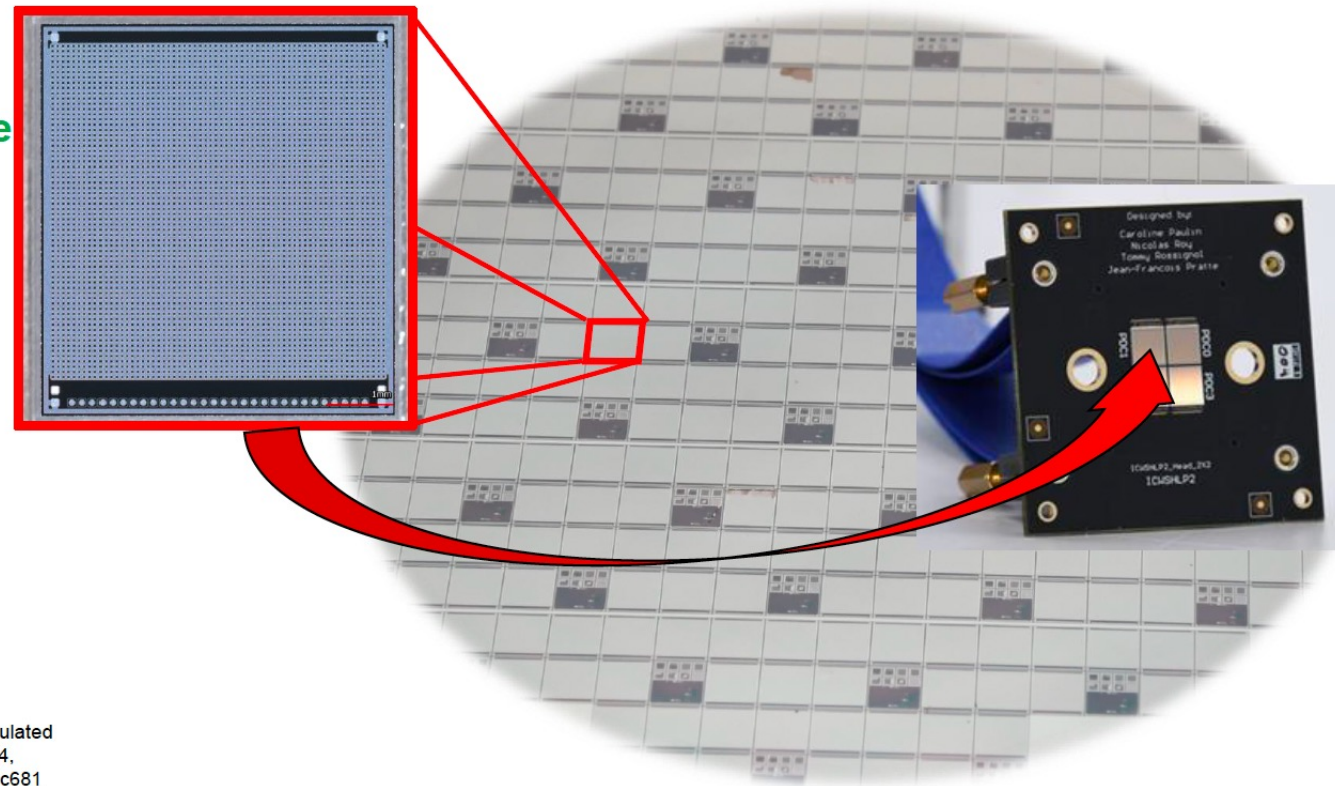
J.-F. PRATTE, S. Parent, S. CHARLEBOIS, and H. DAUTET, "Opto-electrical insulated frontside illuminated 3d digital silicon photomultiplier," US20240113147A1, Apr. 04, 2024
<https://patents.google.com/patent/US20240113147A1/en?q=18%2f526%2c681>

Parent, Samuel, et al. "Single photon avalanche diodes and vertical integration process for a 3D digital SiPM using industrial semiconductor technologies." 2018 IEEE Nuclear Science Symposium and Medical Imaging Conference Proceedings (NSS/MIC). IEEE, 2018.

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Photon-to-Digital Converter on Head:

- 2×2 array of PDCs
- Individual internal quenching circuit:
 - can **enable one SPAD at the time**
 - **programmable** holdoff, recharge
- Shared readout tree:
 - **shared output** (don't know the address of the firing pixel)

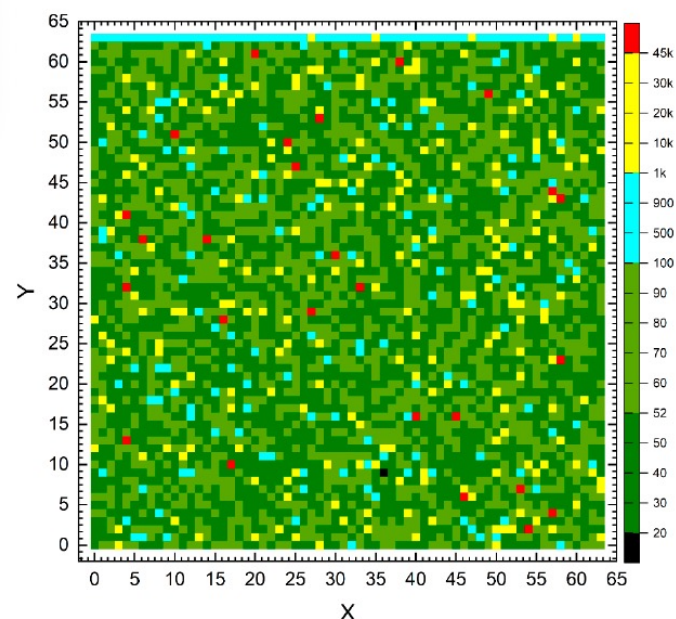


J.-F. PRATTE, S. Parent, S. CHARLEBOIS, and H. DAUTET, "Opto-electrical insulated frontside illuminated 3d digital silicon photomultiplier," US20240113147A1, Apr. 04, 2024 <https://patents.google.com/patent/US20240113147A1/en?q=18%2f526%2c681>

Parent, Samuel, et al. "Single photon avalanche diodes and vertical integration process for a 3D digital SiPM using industrial semiconductor technologies." 2018 IEEE Nuclear Science Symposium and Medical Imaging Conference Proceedings (NSS/MIC). IEEE, 2018.

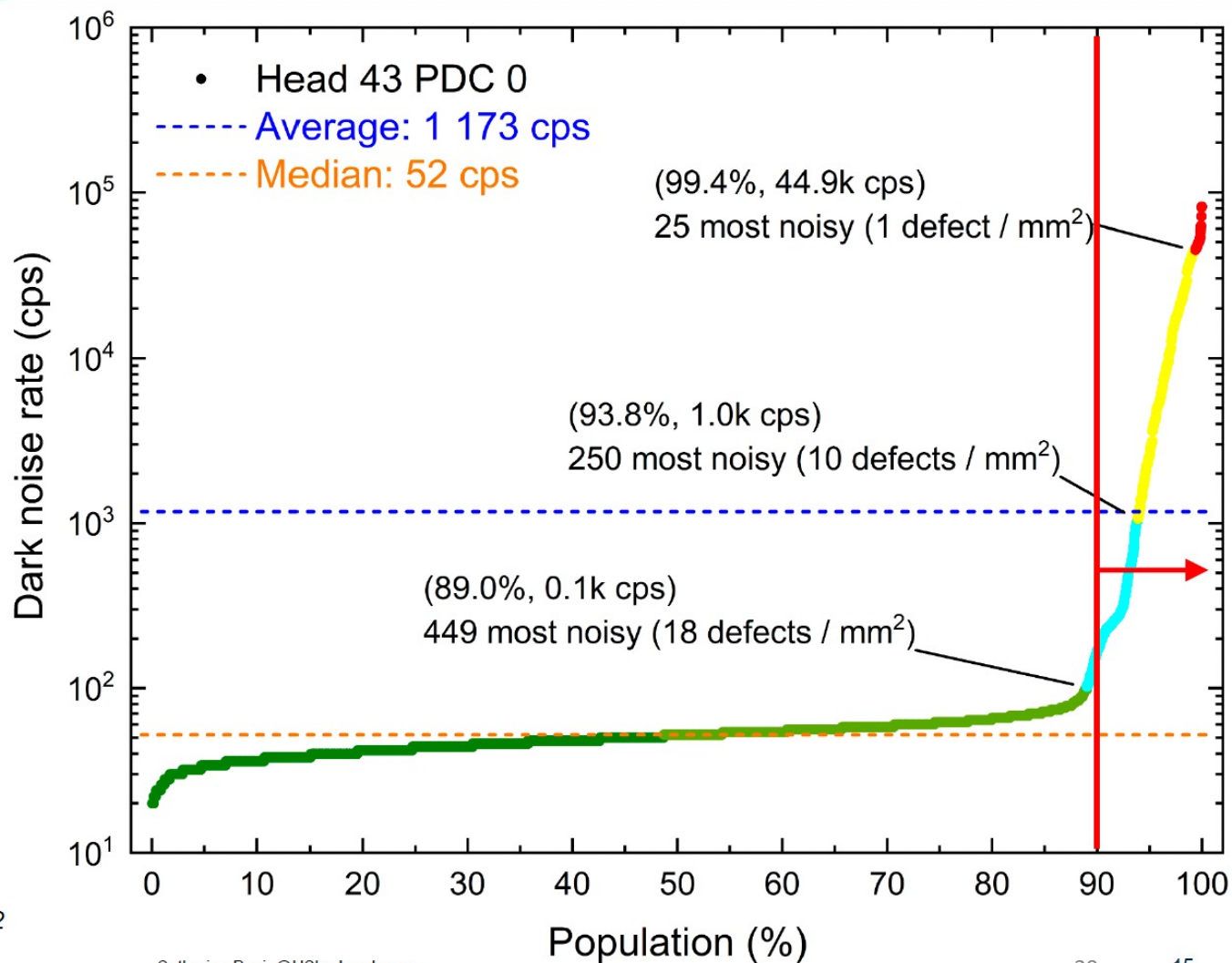
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*Disabling 10% of SPADs
cuts 96% of DCR*



Ø SPADs: 40 μm
100 cps $\rightarrow$ 0.03 cps/ μm^2

PDC

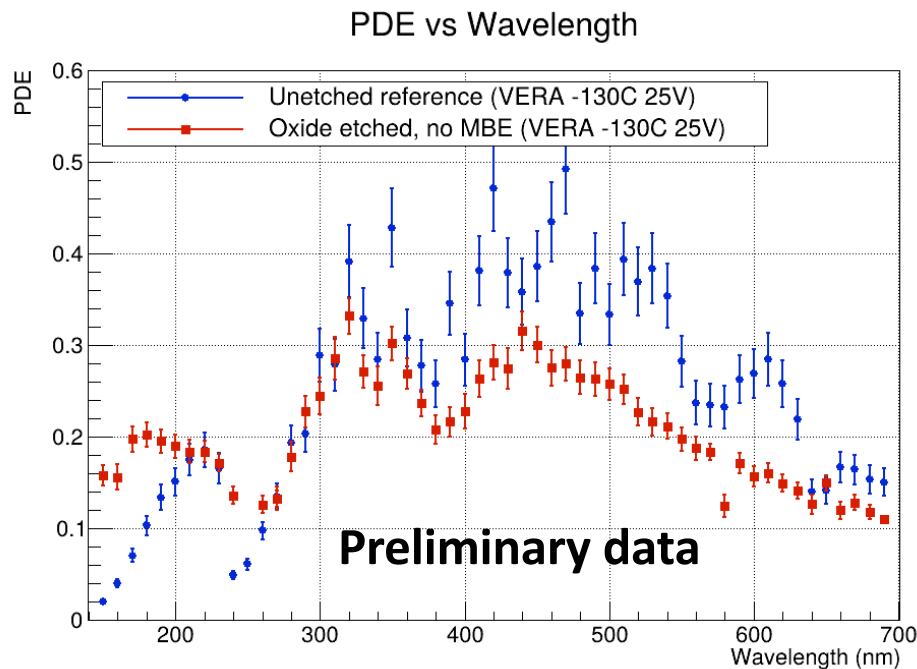


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29

15

PDC for use in Xenon in large quantity



- Validation of the readout scheme at Manchester
- Detailed characterization at TRIUMF
 - With precursors of 3D PDC
- Facility at Teledyne-DALSA (Bromont about 1h drive from here) to be upgraded in 2026

Summary table

Parameter	HPK R11410-21	HPK R12699-406-M4	HPK VUV4	Composite dSiPM
Type	Cylindrical PMT	Square PMT	Square SiPM	Square SiPM
Dimension	$\pi/4 \times 77.5^2 \times 118 \text{ mm}^3$	$56 \times 56 \times 14.8 \text{ mm}^3$	$10 \times 10 \times 0.5 \text{ mm}^3$	$0.8 \times 0.9 \times 0.5 \text{ mm}^3$ [1]
Packing density	61.8%	75%	90%	90%
PDE at 175nm	32.5%	33%	20-25%	20% [2]
Dark count rate	$1.4 \pm 0.7 \text{ Hz/cm}^2$	$0.4 \pm 0.2 \text{ Hz/cm}^2$	50 Hz/cm^2	$\sim 1 \text{ Hz/cm}^2$ [3]
After-pulsing	$8.6 \pm 2.2\%$	$1.1 \pm 0.2\%$	10%	0 using holdoff
Light cross-talk	0	0	0.5%(int.)/2.5%(ext)	?
Th Content	16,000 nBq/cm ²	10,000 nBq/cm ²	0.6 nBq/cm ²	?

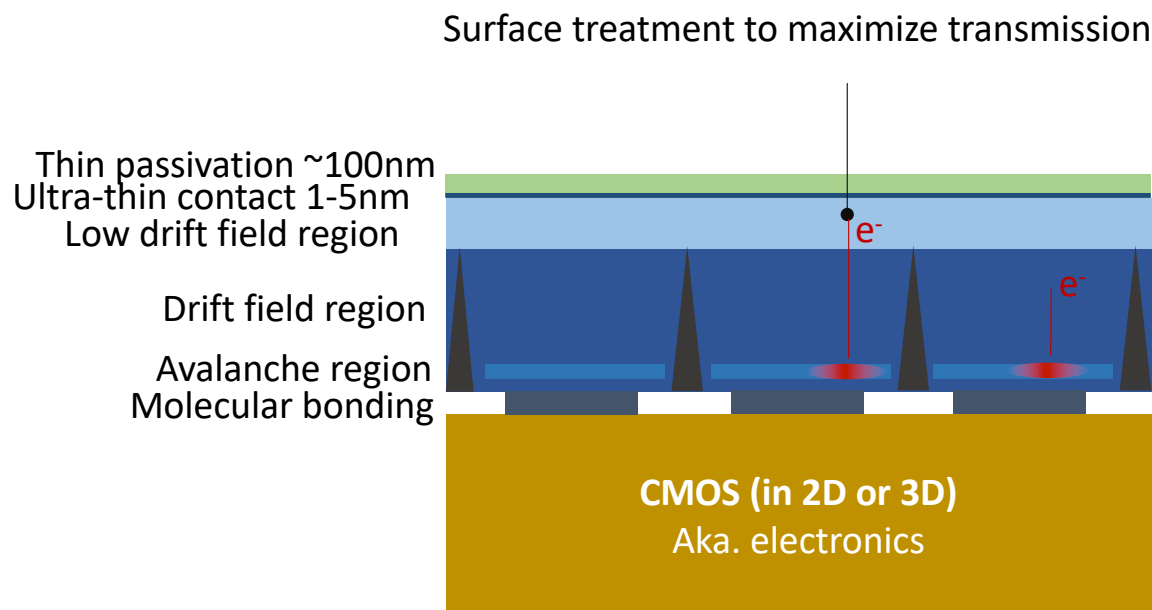
[1] Peter Fischer's DARWIN chip, Fraunhofer

[2] Sherbrooke's low power PDC, DALSA

[3] Fraunhofer 3D digital SiPM with 20% bad pixel masking

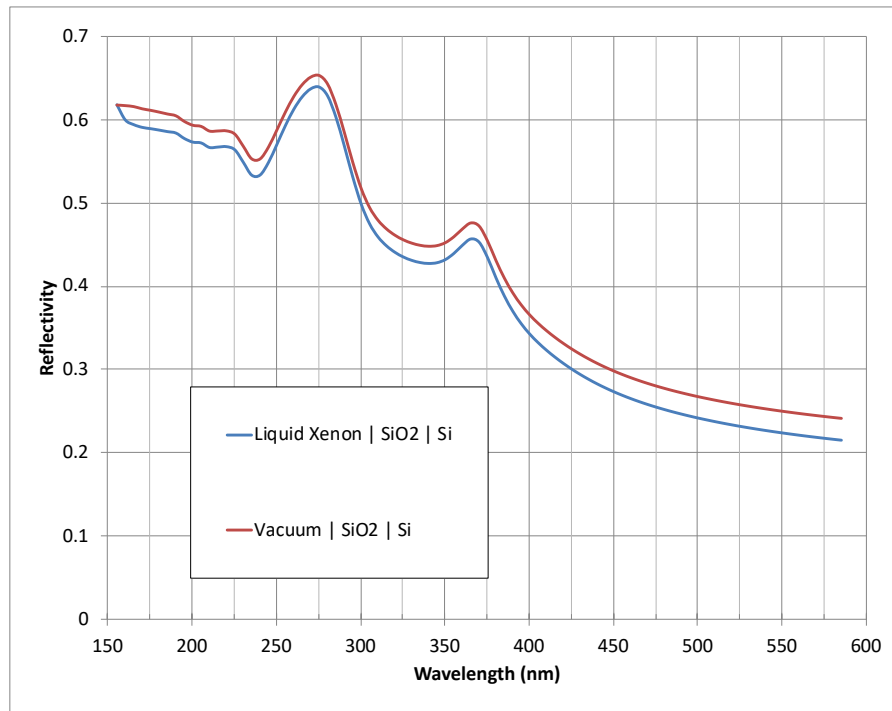
Way forward. The ultimate detector

- SPAD
 - Get to 50% efficiency using Back-side illuminated with VUV surface treatment
 - Use small SPADs
 - Low gain eliminates cross-talk
 - High dynamic range for counting
- Readout
 - Many bits for counting
 - Compromise timing to 10ns if needed
 - Tag first and may be "last" photon per chip
- Get to production scale
 - Teledyne-DALSA 8" line



In Canada?
Or build an intermediate 2D SPAD step?

Way forward – enhancing efficiency for silicon detectors



- Defeating reflections requires an “exotic” solution
 - Graphene (UK groups)
 - Al₂O₃ pillar called black silicon is very promising but fragile
 - Growing pillars in silicon?
 - Embedding wavelength shifter material (Manchester)

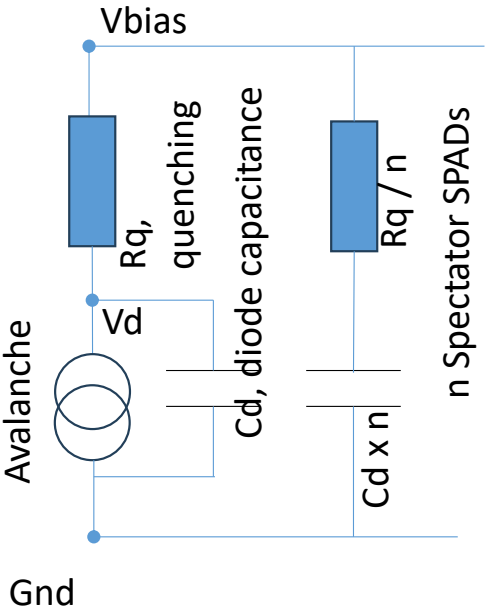
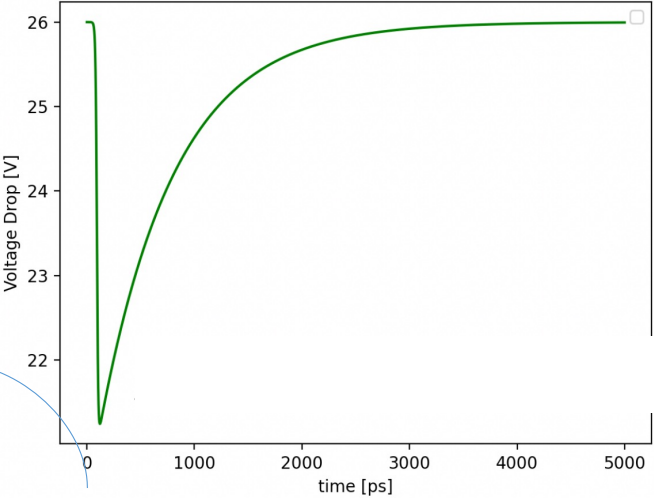
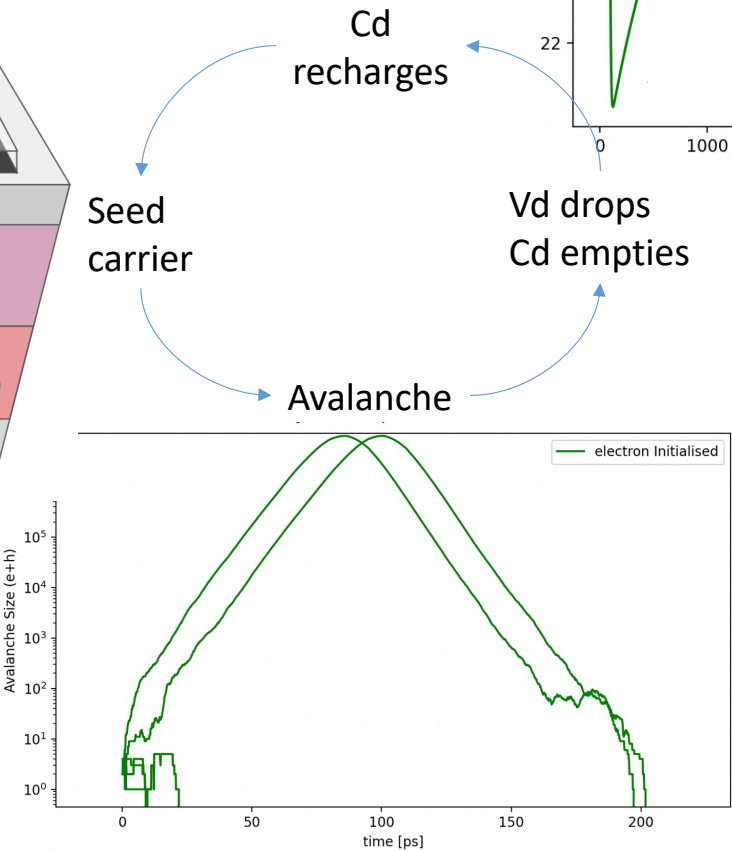
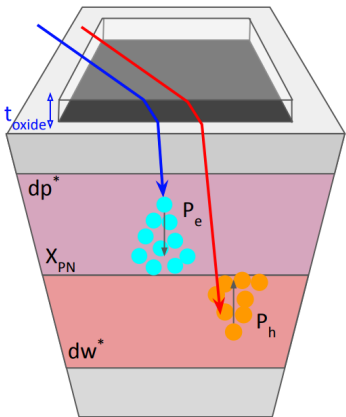
Test all this in a low mass DM + $0\nu\beta\beta$ demonstrator

- Build a LAr or/and LXe double phase TPC
 - Plan for low mass DM with LAr in Canada could hold 3,500 kg of LXe
 - Using ultra-low background digital SiPMs tailored for the application
- Deliverables
 - Low mass DM. Demonstrate the single/few e- threshold with LAr and LXe
 - Demonstrate radiopurity at system level. Use detector itself to gauge background level and validate ICMPs extrapolations
 - Demonstrate ability to handle dynamic range from 1 photons to >1,000 per channel
 - Demonstrate energy resolution. 0.5% FWHM at 2.45 MeV should be achievable

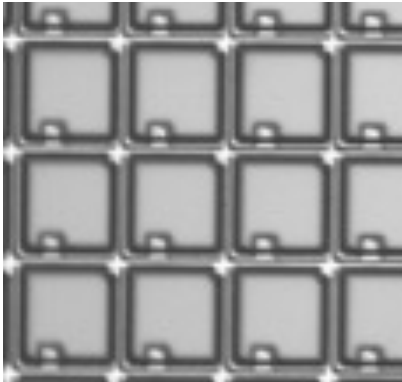
The end
Digital SPAD are the future and
not just for 0vββ



SiPM, Silicon photomultiplier



An array of Single Photon Avalanche Diodes (SPAD)



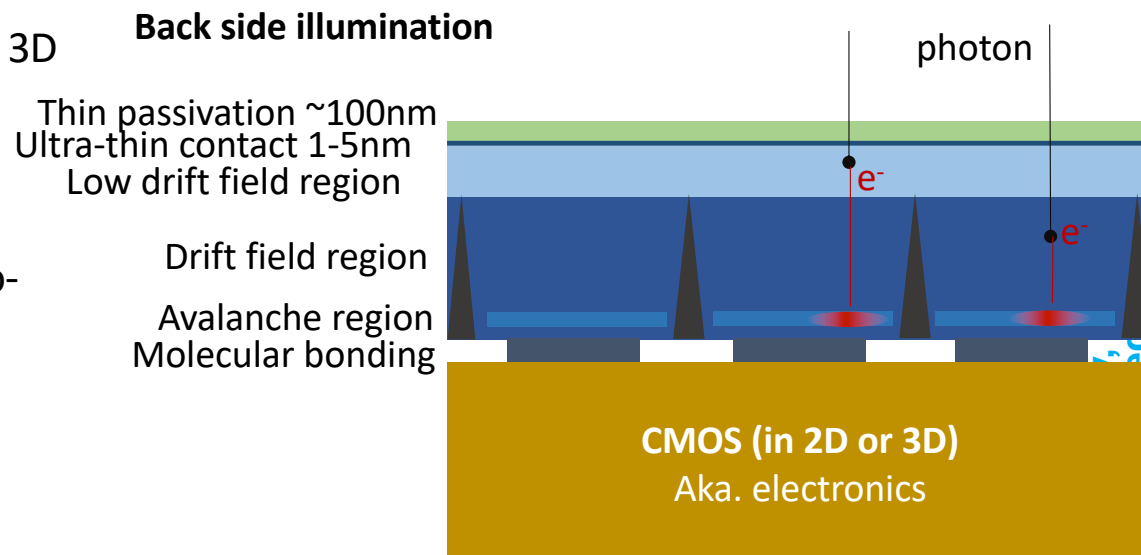
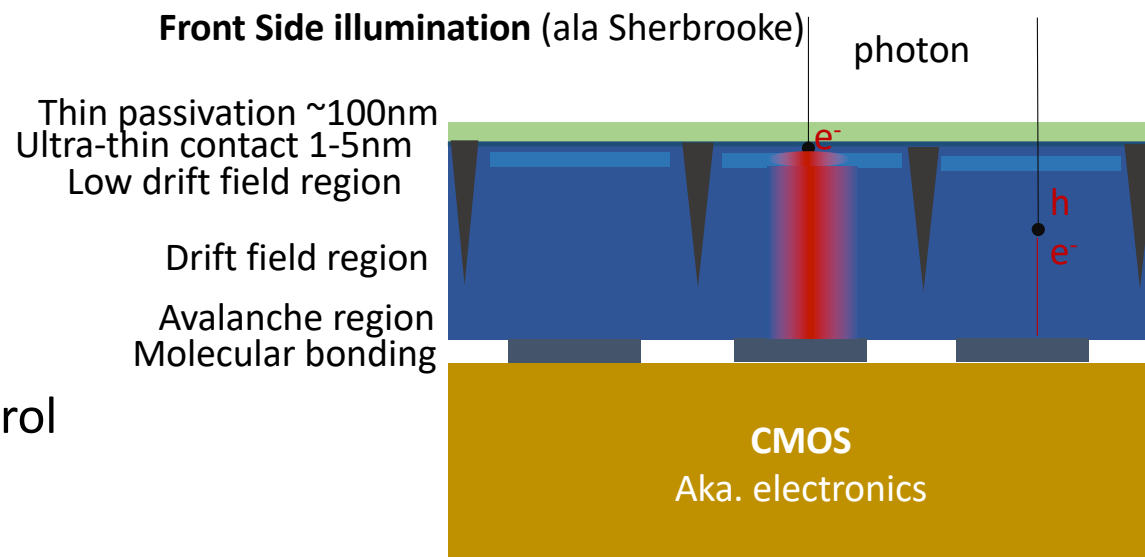
PDC detour

- Versatility

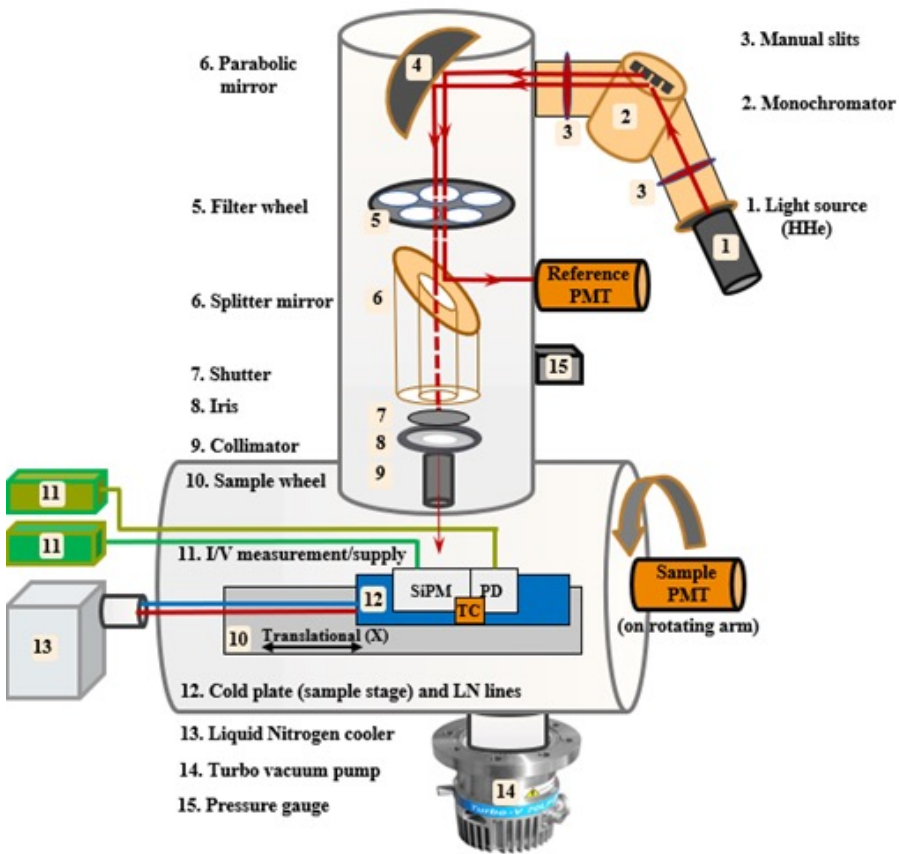
- Visible to IR via thickness control
- Deep UV through Back-side surface processing
 - Unconventional Anti-reflective coating: black silicon, graphene, 3D structures

- Non-photon detection

- Minimum ionizing
- keV scale electron (hybrid photo-detector)
- Dark matter



Asset: Vacuum Ultra-Violet Efficiency reflectivity and Absorption setup (VERA)



For example: inferring the number of electrons produced per VUV photon

